

For Immediate Release

**GENUSION TO SHARE SUPERIOR RELIABILITY FINDINGS
FOR AWARD-WINNING B4-FLASH MEMORY AND LOGIC NVM IP**

**GENUSION To Address NVSMW / ICMTD Conference for Second Consecutive Year:
Company Exploring Productization and IP Business Opportunities**

SAN JOSE, Calif., Monday, May 19, 2008 – GENUSION, Inc., an award-winning pioneer of next generation flash memory technology, announced evaluation findings that demonstrate reliability advantages around its flagship “B4-Flash” and its proprietary Logic NVM “eCFlash” memory technologies. In its second consecutive year, GENUSION has been selected to present its technical papers at the 2008 Joint NVSMW (Nonvolatile Semiconductor Memory Workshop) / ICMTD (International Conference on Memory Technology and Design) Conference. Out of a large number of submissions vying to be chosen, GENUSION was selected to present at the esteemed conference, which will take place at the Club Méditerranée in Opio, France. The conference is scheduled to run from Sunday, May 18th, through Wednesday, May 21st, 2008.

GENUSION’s speaker is scheduled to present on Monday, May 19th at 3:00 p.m. and will discuss the reliability performance around its B4-Flash, which contains experimental results and conclusions around key physical aspects of its capabilities. As GENUSION advances toward bringing B4-Flash closer to productization, the company has been releasing key benchmark milestones that it has achieved. At the 2006 Symposium on VLSI Technology, GENUSION introduced its B4-Flash architecture and discussed its scalability potential. At last year’s NVSMW conference, GENUSION presented operational test findings around B4-Flash’s performance advantages. With reliability being one of the most essential criteria for flash memory, this year GENUSION will present findings that demonstrate B4-Flash’s reliability superiority over existing flash memory technology. GENUSION’S evaluation findings around B4-Flash include its ability to exhibit:

- a 1M memory cycling performance (1,000,000 program/erase cycles)
- a 20-year continuous read operation
- and a 10-year period of data retention at 150degC.

Future B4-Flash target applications include code storage solutions of consumer digital products such as mobile phones, digital cameras, as well as DVD recorders that use flash memory as code storage, where B4-Flash can replace NOR memory and system NAND memory.

Underscoring its broad NVM (non-volatile memory) technology expertise, an additional GENUSION speaker will present reliability findings around its proprietary Logic NVM “eCFlash” on Wednesday, May 21st at 9:20 a.m. eCFlash (embedded CMOS flash) is a new cell architecture IP (intellectual property) that uses standard CMOS logic process — without any additional mask. Because eCFlash uses a charge trap process instead of a floating gate type cell, it is able to achieve very high reliability. Through its testing, GENUSION has verified achieving:

- a 100K cycling performance and
- a 20-year data retention at 150degC, using a 0.25um, 2Kbyte test chip.

These latest findings will enable GENUSION to leverage its eCFlash IP and broaden the application arena for embedded NVM in SoC (System on Chip) compared to existing OTP/MTP (One Time Programmable)/(Multi Time Programmable) IP. Accordingly, GENUSION is now exploring IP business opportunities around its eCFlash technology.

“I’m honored that GENUSION was selected to participate among such an esteemed group of experts and specialists in the memory field. We appreciate the opportunity to update our peers on GENUSION’s progress toward delivering our B4-Flash product to market by the end of 2009 and look forward to exploring IP partnership opportunities,” noted Moriyoshi Nakashima, GENUSION's founder and President.

The 23rd IEEE Nonvolatile Semiconductor Memory Workshop (NVSMW) was recently combined with the 3rd International Conference on Memory Technology and Design (ICMTD). The annual global gathering brings together experts and specialists in all aspects of memory (nonvolatile and volatile) microelectronics.

About GENUSION, Inc.

Founded in 2002, GENUSION is pioneering a breakthrough approach and capability in flash memory technology. Recently awarded ‘Best Future Device Architecture’ at the highly esteemed Mobile Rules! 2008 competition initiated by Nokia, GENUSION’s flagship B4-Flash (Back Bias assisted Band-to-Band tunneling-induced, Hot-Election injection-Flash) technology offers superior programming performance, excellent reliability, and reduces the cost in half compared to conventional NOR flash memory. GENUSION's memory products are built on the company's own memory technologies and SiP design capabilities, in collaboration with leading semiconductor makers, assembly and test manufacturers and sales companies. Based in Amagasaki, Japan, GENUSION is a privately-held company. For more information, interested parties can visit [here](#).

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